In th Claims

Claims 1-24 (Canceled).

25. (Currently Amended): A process of forming MRAM circuitry, comprising:

forming an MRAM cell comprising magnetic material over a substrate;

chemical vapor depositing a silicon carbide comprising layer over the MRAM cell at a temperature of no greater than 500°C;

forming an insulative material over the silicon carbide comprising layer;

etching a contact opening through the insulative material using the silicon carbide comprising layer as an etch stop; and

plasma etching within the contact opening through the silicon carbide comprising layer using a gas chemistry comprising oxygen and hydrogen to extend the contact opening through the silicon carbide comprising layer to the magnetic material of the MRAM cell, and under conditions which ~~etches~~ etch the silicon carbide comprising layer at a rate at least twice that of any etching of the insulative material.

26. (Original): The method of claim 25 wherein the MRAM cell comprises a dielectric layer sandwiched between magnetic material layers.

27. (Original): The method of claim 25 wherein the insulative material comprises SiO_2.

28. (Original): The method of claim 25 comprising conducting the chemical vapor depositing at a temperature of no greater than 200°C.

29. (Original): The method of claim 25 wherein the substrate is not exposed to a temperature greater than 500°C between the depositing and the etching.

30. (Original): The method of claim 25 wherein the substrate is not exposed to a temperature greater than the highest temperature during the depositing between the depositing and the etching.

31. (Original): The method of claim 25 comprising conducting the chemical vapor depositing at a temperature of no greater than 250°C, and wherein the substrate is not exposed to a temperature greater than 250°C between the depositing and the etching.

32. (Original): The method of claim 25 wherein the oxygen is derived from the group consisting of O_2, O_3, NO_x, CO, CO_2, and mixtures thereof.

33. (Original): The method of claim 25 wherein the hydrogen is derived from the group consisting of H_2, NH_3, CH_4, and mixtures thereof.

34. (Original): The method of claim 25 wherein the plasma etching is conducted within a chamber, plasma during the plasma etching being first formed within the chamber.

35. (Original): The method of claim 25 comprising after the plasma etching, forming conductive material within the contact opening.

Claims 36-47 (Canceled).

48. (New): The method of claim 25 wherein the chemical vapor depositing is plasma enhanced.

49. (New): The method of claim 25 wherein,

the oxygen is derived from the group consisting of O_2, O_3, NO_x, CO, CO_2, and mixtures thereof; and

the hydrogen is derived from the group consisting of H_2, NH_3, CH_4, and mixtures thereof.

50. (New): The method of claim 25 wherein the oxygen is derived at least in part from O_2 and the hydrogen is derived at least in part from NH_3.

51. (New): The method of claim 25 wherein the plasma etching is conducted within a chamber, plasma during the plasma etching being first formed remote from the chamber.

52. (New): The method of claim 25 comprising plasma etching under conditions which etch the silicon carbide comprising layer at a rate at least three times that of any etching of the insulative material.

53. (New): The method of claim 25 comprising plasma etching under conditions which etch the silicon carbide comprising layer at a rate at least four times that of any etching of the insulative material.

54. (New): The method of claim 25 wherein the oxygen is derived from a gas comprising O_2.

55. (New): The method of claim 25 wherein the oxygen is derived from a gas comprising O_3.

56. (New): The method of claim 25 wherein the oxygen is derived from a gas comprising NO_x.

57. (New): The method of claim 25 wherein the oxygen is derived from a gas comprising CO.

58. (New): The method of claim 25 wherein the oxygen is derived from a gas comprising CO_2.

59. (New): The method of claim 25 wherein the hydrogen is derived from a gas comprising H_2.

60. (New): The method of claim 25 wherein the hydrogen is derived from a gas comprising NH_3.

61. (New): The method of claim 25 wherein the hydrogen is derived from a gas comprising CH_4.